

AMENDMENTS TO THE CLAIMS

1. (Currently Amended) A plating method comprising:
preparing a substrate having a relatively narrow recess and a relatively broad recess defined in a surface thereof;
performing first plating under plating conditions for filling a metal in ~~said~~ the narrow recess to form a plated film; and then
applying a reverse electric field in a manner so as to etch the plated film filled in the narrow recess by said performing said first plating; and then
performing second plating under plating conditions for filling a metal in ~~said~~ the broad recess.
2. (Currently Amended) A plating method according to claim 1, wherein entire surfaces of ~~said~~ the narrow recess and ~~said~~ the broad recess are fully covered with a seed layer.
3. (Original) A plating method according to claim 1, wherein said first plating is performed under plating conditions for a relatively high bottom-up capability, and said second plating is performed under plating conditions for a relatively high leveling capability.
4. (Currently Amended) A plating method according to claim 1, wherein ~~said~~ the narrow recess has a width less than 0.2 μm and ~~said~~ the broad recess has a width of 0.2 μm or greater.
5. (Currently Amended) A plating method according to claim 1, wherein ~~said~~ the substrate has a plurality of ~~said~~ narrow recesses defined in the surface thereof.
6. (Currently Amended) A plating method according to claim 1, wherein ~~said~~ the substrate has a plurality of ~~said~~ broad recesses defined in the surface thereof.

7. (Currently Amended) A plating method according to claim 1, wherein said first plating and said second plating are performed under different plating conditions including different current densities ~~upon~~ during plating.

8. (Currently Amended) A plating method according to claim 7, wherein said second plating ~~process~~ is performed under plating conditions including a current density which is higher than a currently density during said first plating.

9. (Currently Amended) A plating method according to claim 8, wherein said first plating is performed under plating conditions including a current density ~~upon~~ during plating ranging from 0.1 A/dm² to 1.5 A/dm², and said second plating is performed under plating conditions including a current density upon plating ranging from 2 A/dm² to 7 A/dm².

Claims 10-26 (Cancelled).

27. (New) A plating method according to claim 1, wherein said reverse electric field is applied for a period of time in a range of 1 second to 10 seconds.